# Abstracts

## Silicon Avalanche-Diode Microstrip L-Band Oscillator (Correspondence)

*A. Rosen and J. Assour. "Silicon Avalanche-Diode Microstrip L-Band Oscillator (Correspondence)." 1970 Transactions on Microwave Theory and Techniques 18.11 (Nov. 1970 [T-MTT] (Special Issue on Microwave Circuit Aspects of Avalanche-Diode and Transferred Electron Devices)): 979-981.*

A metal ceramic microstrip oscillator circuit using high-efficiency silicon avalanche diodes mounted in capacitively loaded transverse-electromagnetic (TEM) coupled lines is described. The physical dimensions of the oscillator circuit are 1.5 by 1.0 by 0.5 inches high. Results achieved at L-band are 105 watts peak output at 1.5 GHz with 13-percent efficiency.

❑ Return to main document.